SHINDENGEN

Switching Power Transistor

LSV Series

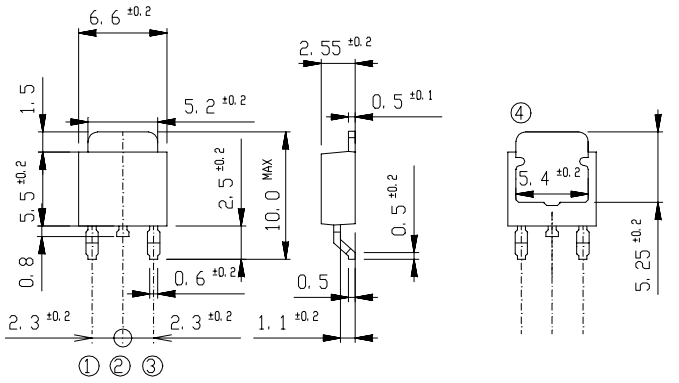
2SA1796
(TE7T4)

-7A PNP

OUTLINE DIMENSIONS

Case : E-pack

Unit : mm



RATINGS

●Absolute Maximum Ratings

Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	Tstg		−55～150	℃
Junction Temperature	Tj		150	℃
Collector to Base Voltage	V_{CBO}		−60	V
Collector to Emitter Voltage	V_{CEO}		−40	V
Emitter to Base Voltage	V_{EBO}		−7	V
Collector Current DC	I_C		−7	A
Collector Current Peak	I_{CP}		−14	A
Base Current DC	I_B		−1.5	A
Base Current Peak	I_{BP}		−2	A
Total Transistor Dissipation	P_T	Tc = 25℃	10	W

●Electrical Characteristics (Tc=25℃)

Item	Symbol	Conditions	Ratings	Unit
Collector to Emitter Sustaining Voltage	V_{CEO}(sus)	I_C = −0.1A	Min −40	V
Collector Cutoff Current	I_{CBO}	At rated Voltage	Max −0.1	mA
	I_{CEO}		Max −0.1	
Emitter Cutoff Current	I_{EBO}	At rated Voltage	Max −0.1	mA
DC Current Gain	h_{FE}	V_{CE} = −2V, I_C = −3.5A	Min 70	
Collector to Emitter Saturation Voltage	V_{CE}(sat)	I_C = −3.5A	Max −0.3	V
Base to Emitter Saturation Voltage	V_{BE}(sat)	I_B = −0.2A	Max −1.2	V
Thermal Resistance	θ jc	Junction to case	Max 12.5	℃/W
Transition Frequency	f_T	V_{CE} = −10V, I_C = −0.7A	TYP 50	MHz
Turn on Time	ton	I_C = −3.5A I_{B1} = −0.35A, I_{B2} = −0.35A R_L = 8Ω, V_{BB2} = −4V	Max 0.3	μs
Storage Time	ts		Max 1.5	
Fall Time	tf		Max 0.5	

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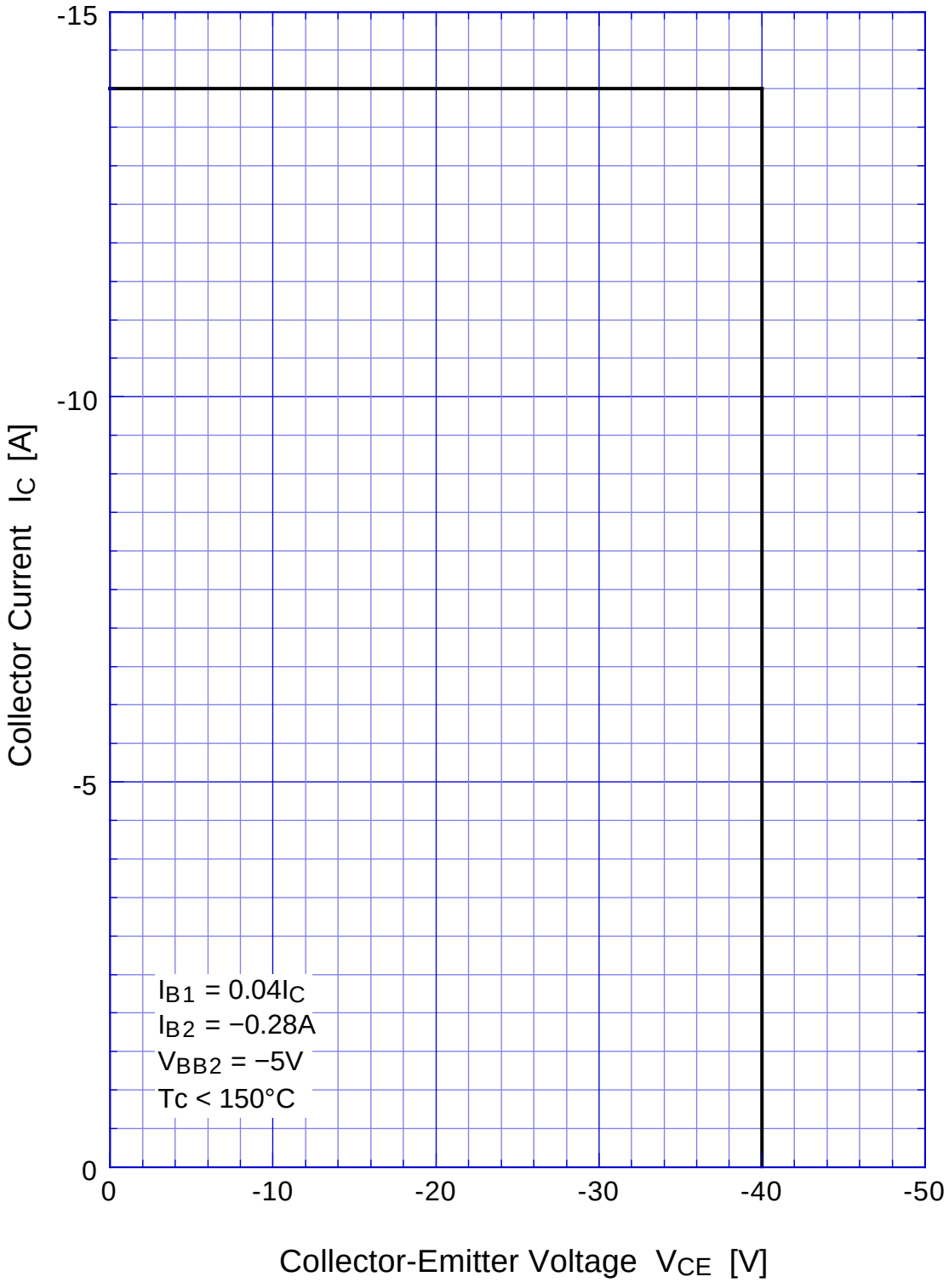
2SA1796 Reverse Bias SOA